

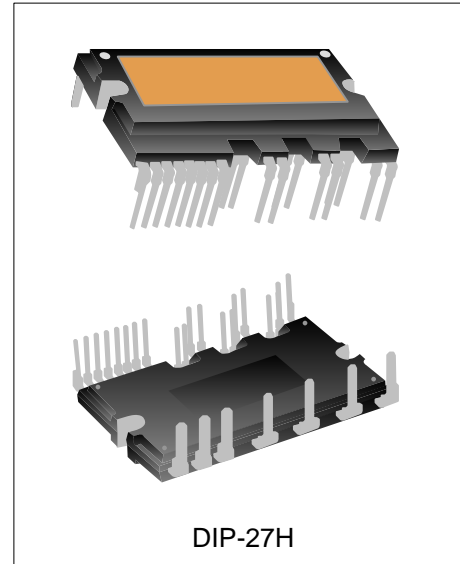
## 600V/15A 3-PHASE FULL-BRIDGE DRIVER (INTELLIGENT POWER MODULE)

### DESCRIPTION

SD15M60AC is a 3-phase brushless DC motor driver with high integration and high reliability for low power inverter driving such as air condition, dishwasher, and industrial sewing machine. It has embedded six low-loss IGBT and three high-speed half-bridge gate drivers with high voltage.

The under voltage, short circuit and over temperature protections integrated make the circuit work safely in a wide range. The current of each phase can be detected separately because there is one independent negative DC terminal for each phase.

SD15M60AC uses high-insulation design, compact package and carries heat easily, which makes it easy to use especially for compact installation applications.



### FEATURES

- ◆ Built-in low-loss 600V/15A IGBT;
- ◆ Built-in high-voltage gate driver;
- ◆ Built-in under voltage, over temperature and over current protections;
- ◆ Built-in bootstrap diode;
- ◆ Compatible with 3.3V, 5V MCU interface, active high;
- ◆ Three independent negative DC terminal for inverter current detection;
- ◆ Alarm signal: for low-side under voltage and short circuit protections;
- ◆ Package in DBC design with low thermal resistance;
- ◆ Insulation level: 2500Vrms/min

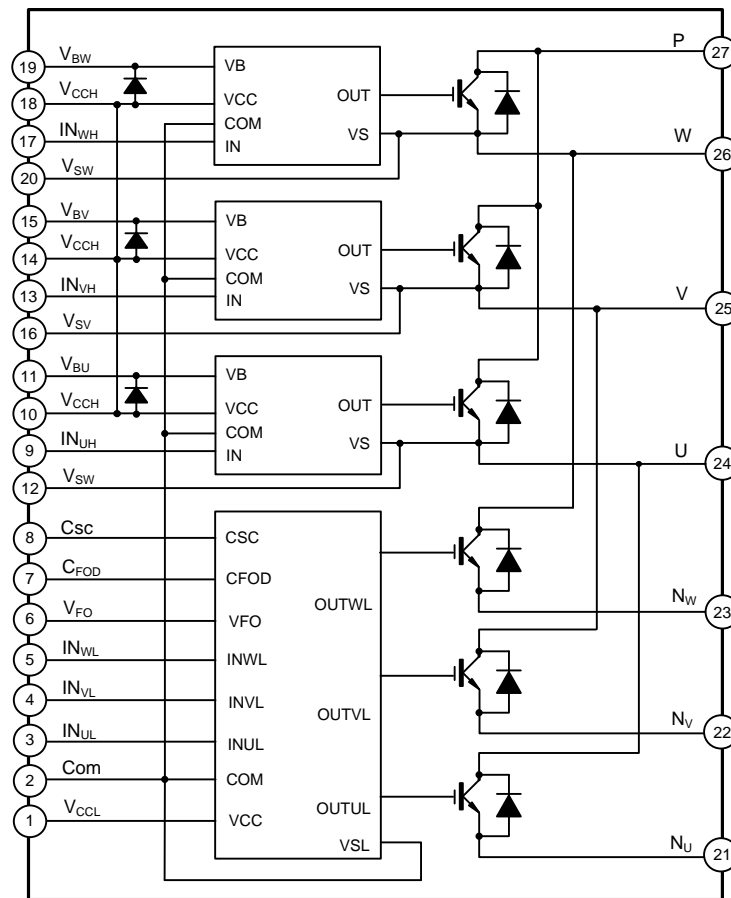
### APPLICATIONS

- ◆ Air condition compressor
- ◆ Refrigerator compressor
- ◆ Low power inverter
- ◆ Industrial sewing machine

### ORDERING INFORMATION

Part No.	Package	Marking	Hazardous Substance Control	Packing Type
SD15M60AC	DIP-27H	SD15M60AC	Halogen free	Tube

**BLOCK DIAGRAM**



**ABSOLUTE MAXIMUM RATING**

Characteristics	Symbol	Rating	Unit
<b>Inverter section</b>			
Voltage on the DC bus between PN	$V_{PN}$	450	V
Surge voltage on the DC bus between PN	$V_{PN(Surge)}$	500	V
Voltage between collector and emitter	$V_{CES}$	600	V
Continuous current of the single IGBT collector, $T_C=25^\circ\text{C}$	$I_C$	15	A
Peak current of the single IGBT collector, $T_C=25^\circ\text{C}$ , Pulse width less than 1ms	$I_{CP}$	30	A
Max. power dissipation of the collector of each module, $T_C=25^\circ\text{C}$	$P_C$	55	W
<b>Control section</b>			
Control supply voltage	$V_{CC}$	20	V
High-side control voltage	$V_{BS}$	20	V
Input signal voltage	$V_{IN}$	-0.3~17	V
Fault output supply voltage	$V_{FO}$	-0.3~ $V_{CC}+0.3$	V

Characteristics	Symbol	Rating	Unit
Fault output current Sink current at V <sub>FO</sub> pin	I <sub>FO</sub>	5	mA
Input voltage at current detect pin	V <sub>SC</sub>	-0.3~V <sub>CC</sub> +0.3	V
<b>Whole system</b>			
Voltage limit of short circuit protection V <sub>CC</sub> =V <sub>BS</sub> =13.5~16.5V, T <sub>J</sub> =150°C, single and less than 2μs	V <sub>PN(PROT)</sub>	400	V
Operating temperature of module case Limit condition: -40°C≤T <sub>J</sub> ≤150°C	T <sub>C</sub>	-40~125	°C
Storage temperature range	T <sub>STG</sub>	-40~150	°C
Junction-to-case thermal resistance of each IGBT	R <sub>θJCQ</sub>	2.27	°C/W
Junction-to-case thermal resistance of each FRD	R <sub>θJCF</sub>	3.0	°C/W
Insulation voltage 60Hz, Sine, 1 minute Connect the pin to heatsink	V <sub>ISO</sub>	2500	V <sub>rms</sub>
Mounting torque Mounting screws: -M3, 0.62N.m recommended	T	0.5~0.8	N.m
Bootstrap Diode Forward Current, T <sub>C</sub> =25°C	I <sub>F</sub>	0.5	A
Bootstrap Diode Forward Current(Peak), T <sub>C</sub> =25°C, Under 1ms Pulse Width	I <sub>FP</sub>	2.0	A

## RECOMMENDED OPERATING CONDITIONS

Characteristics	Symbol	Ratings			Unit
		Min.	Typ.	Max.	
Voltage on the bus between PN	V <sub>PN</sub>	--	300	400	V
Control supply voltage	V <sub>CC</sub>	13.5	15	16.5	V
High-side control voltage	V <sub>BS</sub>	13.5	15	16.5	V
Control voltage variation	dV <sub>CC</sub> /dt dV <sub>BS</sub> /dt	-1	--	1	V/μs
On threshold voltage	V <sub>IN(ON)</sub>	3.0	--	V <sub>CC</sub>	V
Off threshold voltage	V <sub>IN(OFF)</sub>	0	--	0.6	V
Blanking time for preventing arm- short V <sub>CC</sub> =V <sub>BS</sub> =13.5~16.5V, T <sub>J</sub> ≤25°C	T <sub>dead</sub>	2.0	--	--	μs
PWM input signal	f <sub>PWM</sub>	--	--	20	KHz
Voltage on current detecting pin	V <sub>SEN</sub>	-4	--	4	V

**ELECTRICAL CHARACTERISTICS(UNLESS OTHERWISE SPECIFIED,  $T_{amb}=25^{\circ}C$ ,  $V_{CC}=V_{BS}=15V$ )**

**Inverter**

Characteristics		Symbol	Conditions	Min.	Typ.	Max.	Unit
Saturation voltage between collector and emitter		$V_{CE(SAT)}$	$V_{CC}=V_{BS}=15V$ , $V_{IN}=5V$ $I_C=15A$ , $T_J=25^{\circ}C$	--	--	2.3	V
FRD forward voltage		$V_F$	$V_{IN}=0V$ , $I_F=15A$ , $T_J=25^{\circ}C$	--	--	2.3	V
Switching times	High side	$t_{ON}$	$V_{PN}=300V$ , $V_{CC}=V_{BS}=15V$ , $I_C=15A$ , $V_{IN}=0V \leftrightarrow 5V$ , Inductive load Refer to fig. 1	--	0.85	--	$\mu s$
		$t_{C(ON)}$		--	0.20	--	$\mu s$
		$t_{OFF}$		--	0.63	--	$\mu s$
		$t_{C(OFF)}$		--	0.15	--	$\mu s$
	Low side	$t_{ON}$		--	0.50	--	$\mu s$
		$t_{C(ON)}$		--	0.20	--	$\mu s$
		$t_{OFF}$		--	0.25	--	$\mu s$
		$t_{C(OFF)}$		--	0.15	--	$\mu s$
		$t_{rr}$	--	0.06	--	$\mu s$	
Leakage current between collector and emitter		$I_{CES}$	$V_{CE}=V_{CES}$	--	--	1	mA

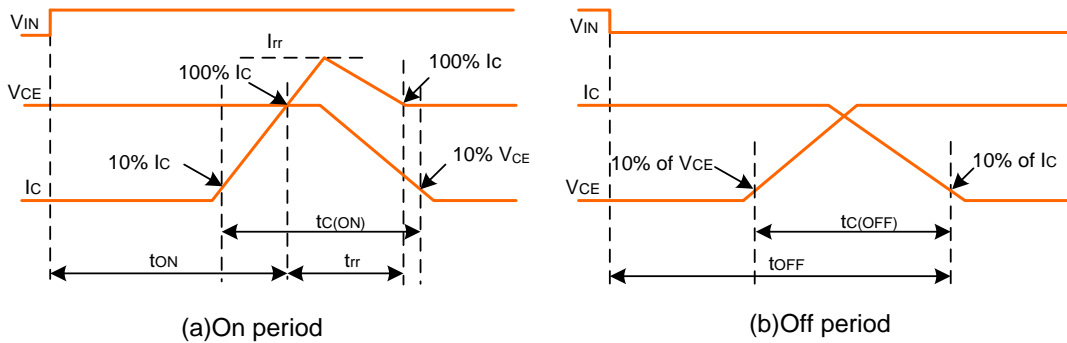


Fig.1 Switching definition

**Control section**

Characteristics		Symbol	Conditions	Min.	Typ.	Max.	Unit
$V_{CC}$ Quiescent current	$I_{QCCL}$	$V_{CC}=15V$ , $V_{INL}=0V$	Between $V_{CCL}$ and COM	--	--	28	mA
	$I_{QCCH}$	$V_{CC}=15V$ , $V_{INH}=0V$	Between $V_{CCH}$ and COM	--	--	600	$\mu A$
$V_{BS}$ Quiescent current	$I_{QBS}$	$V_{BS}=15V$ , $V_{INH}=0V$	$V_{BU}-V_{SU}$ , $V_{BV}-V_{SV}$ , $V_{BW}-V_{SW}$	--	--	500	$\mu A$
Fault output voltage	$V_{FOH}$	$V_{SC}=0V$ , $V_{FO}$ pull up 4.7K $\Omega$ resistor to 5V		4.5	--	--	V
	$V_{FOL}$	$V_{SC}=1V$ , $V_{FO}$ pull up 4.7K $\Omega$ resistor to 5V		--	--	0.8	V
Fault output pulse width	$t_{FO}$	$C_{FO}=33nF$	(note1)	1.0	1.8	--	ms

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit	
Trip voltage of short circuit	$V_{SC(ref)}$	$V_{CC}=15V$ (note2)	0.45	0.5	0.55	V	
Over-temperature protection	TSD	LVIC temperature	--	160	--	°C	
Over-temperature protection hysteresis	$\Delta TSD$	LVIC temperature	--	10	--	°C	
Low-side under voltage protection (fig.4)	$UV_{CCD}$	$V_{CC}$ detect voltage	10.4	11.4	12.4	V	
	$UV_{CCR}$	$V_{CC}$ reset voltage	10.9	11.9	12.9	V	
High-side under voltage protection (fig.5)	$UV_{BSD}$	$V_{BS}$ detect voltage	10.0	11.0	12.0	V	
	$UV_{BSR}$	$V_{BS}$ reset voltage	10.5	11.5	12.5	V	
On threshold voltage	$V_{IH}$	Logic High	Between input and COM	2.8	--	--	V
Off threshold voltage	$V_{IL}$	Logic Low		--	--	0.9	V

**Note1:** Fault output pulse width  $t_{FO}$  is decided by  $C_{FOD}$  and  $C_{FO}=18.3 \times 10^{-6} \times t_{FO}[F]$

**Note2:** Short circuit protection is functioning only at the low-sides.

**Bootstrap Diode Part(Each Bootstrap diode, Unless Otherwise Specified)**

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Voltage	$V_F$	$I_F=0.1A, T_C=25^\circ C$	--	2.5	--	V
Reverse Recovery Time	$t_{rr}$	$I_F=0.1A, T_C=25^\circ C$	--	80	--	ns

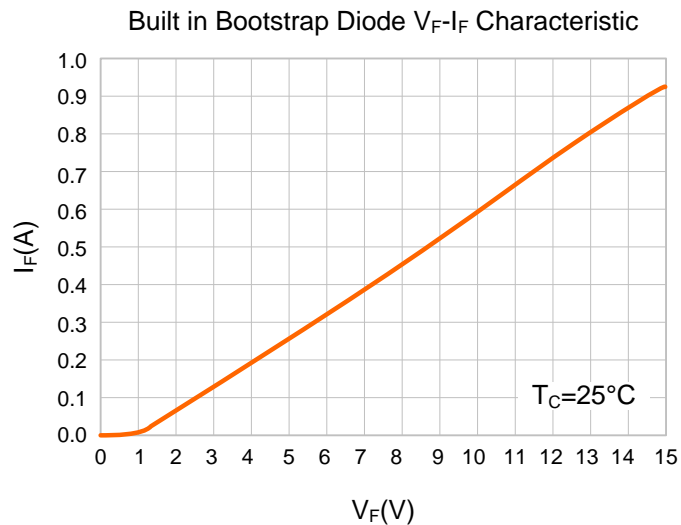
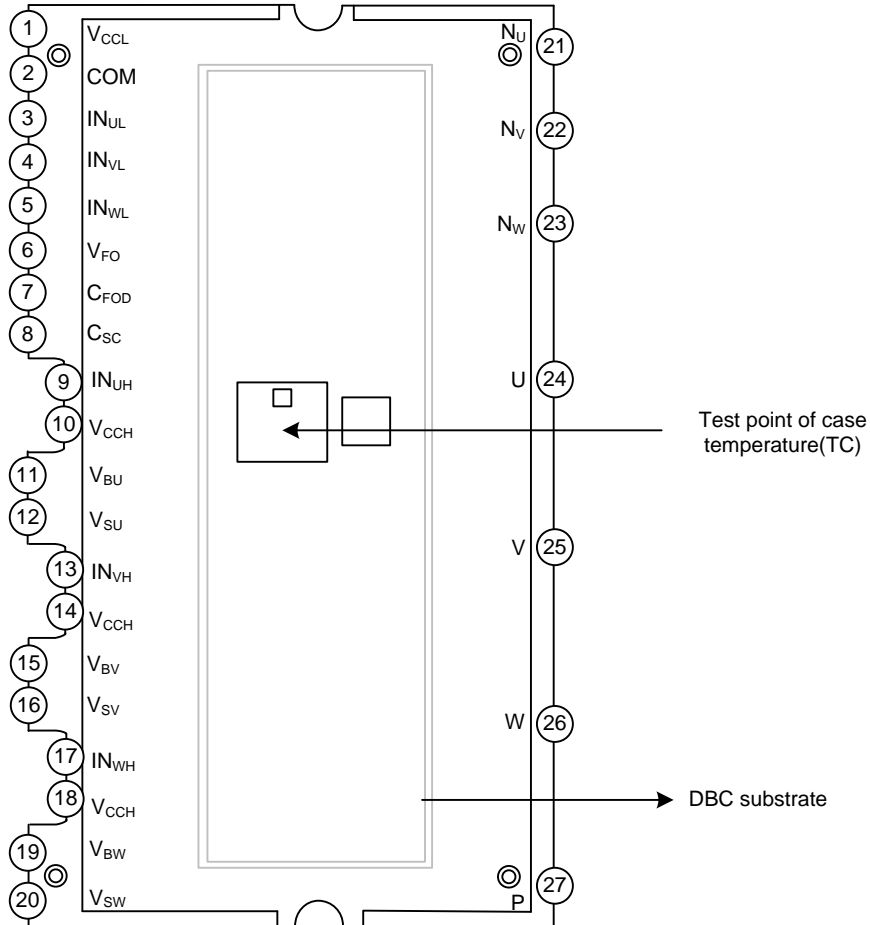


Fig.2 Built in Bootstrap Diode  $V_F$ - $I_F$  Characteristic

**Note:** Resistive characteristic: equivalent resistor: ~ 15Ω.

**PIN CONFIGURATION**



## PIN DESCRIPTION

Pin No.	Pin Name	Pin Descriptions
1	V <sub>CCL</sub>	Supply voltage for low-side gate driver
2	COM	Common ground for the module
3	IN <sub>UL</sub>	U-phase low-side signal input
4	IN <sub>VL</sub>	V-phase low-side signal input
5	IN <sub>WL</sub>	W-phase low-side signal input
6	V <sub>FO</sub>	Fault output
7	C <sub>FOD</sub>	Connect to the capacitor to adjust the duration time of fault output
8	C <sub>SC</sub>	Connect to the capacitor for short circuit current detection input and low-pass filter
9	IN <sub>UH</sub>	U-phase high-side signal input
10	V <sub>CCH</sub>	Supply voltage for high-side gate driver
11	V <sub>BU</sub>	Floating supply voltage for U-phase high-side IGBT driving
12	V <sub>SU</sub>	Floating ground for U-phase high-side IGBT driving
13	IN <sub>VH</sub>	V-phase high-side signal input
14	V <sub>CCH</sub>	Supply voltage for high-side gate driver
15	V <sub>BV</sub>	Floating supply voltage for V-phase high-side IGBT driving
16	V <sub>SV</sub>	Floating ground for V-phase high-side IGBT driving
17	IN <sub>WH</sub>	W-phase high-side signal input
18	V <sub>CCH</sub>	Supply voltage for high-side gate driver
19	V <sub>BW</sub>	Floating supply voltage for W-phase high-side IGBT driving
20	V <sub>SW</sub>	Floating ground for W-phase high-side IGBT driving
21	N <sub>U</sub>	U-phase DC negative terminal
22	N <sub>V</sub>	V-phase DC negative terminal
23	N <sub>W</sub>	W-phase DC negative terminal
24	U	U-phase output
25	V	V-phase output
26	W	W-phase output
27	P	DC positive terminal

**CONTROL TIMING SEQUENCE DESCRIPTION**

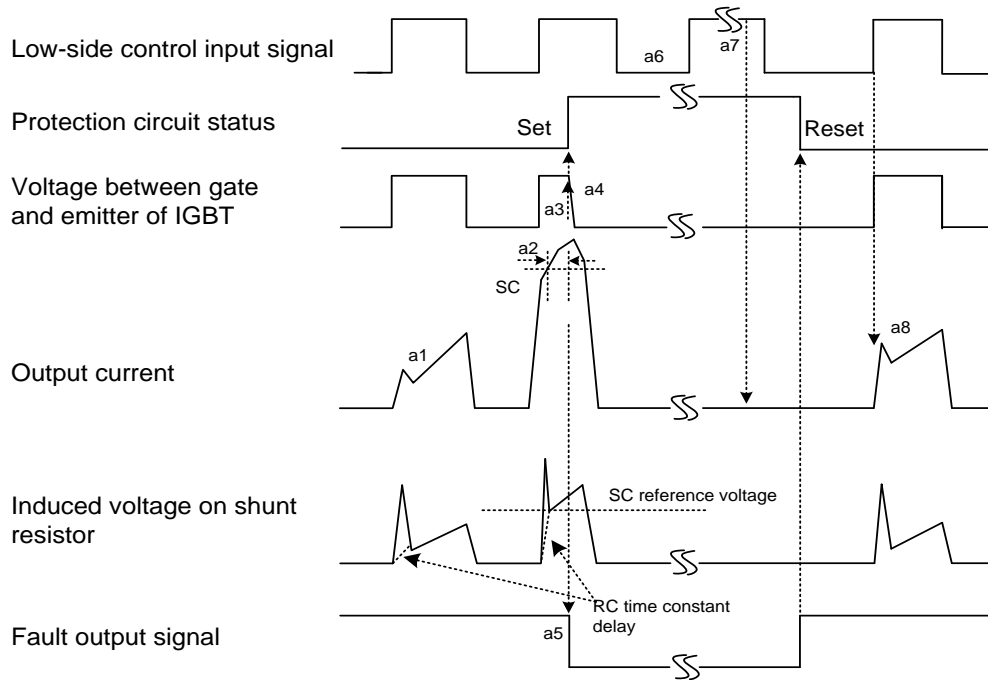


Fig.3 Timing sequence for short circuit current protection (only for low-side)

( Including the external shunt resistor and RC connection)

- a1: Normal operation: IGBT turn on and carrying current.
- a2: Short circuit current detect (SC trigger).
- a3: IGBT gate hard interrupt.
- a4: IGBT turns off.
- a5: Fault output timer starts working: the pulse width of fault output signal is decided by external capacitor CFO.
- a6: Input "L": IGBT off state.
- a7: Input "H": IGBT on state, but during the active period of fault output, the IGBT doesn't turn ON.
- a8: Normal operation: IGBT turn on and carrying current.



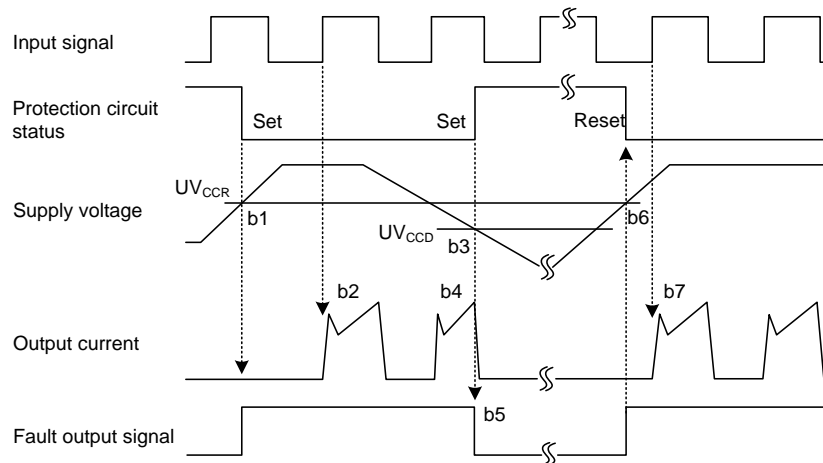


Fig.4 Timing sequence for under voltage protection( low-side)

- b1: Supply voltage rises to  $UV_{CCR}$ , the circuit start to operate when next input waveform arrives.
- b2: Normal operation: IGBT turn on and carrying current.
- b3: Under voltage detect point ( $UV_{CCD}$ ).
- b4: IGBT is off no matter what signal is input.
- b5: Fault output operation starts.
- b6: Under voltage reset ( $UV_{CCR}$ ).
- b7: Normal operation: IGBT turn on and carrying current.

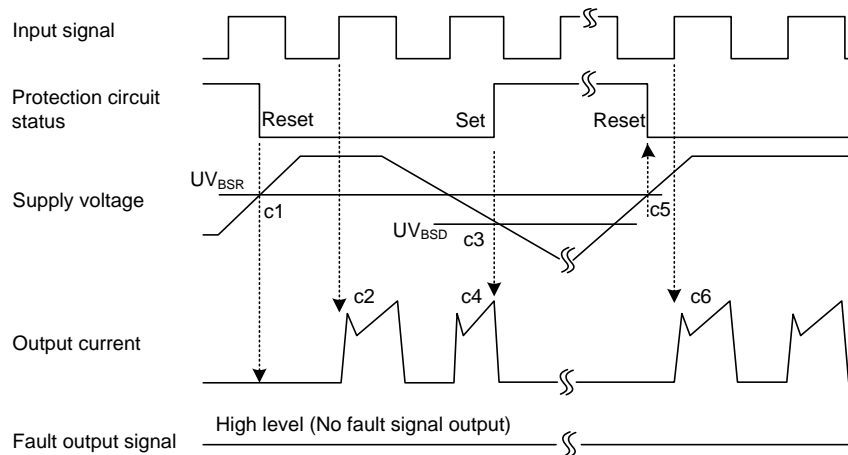


Fig.5 Timing sequence for under voltage protection ( high-side)

- c1: Supply voltage rises to  $UV_{BSR}$ , the circuit start to operate when next input signal arrives.
- c2: Normal operation: IGBT turn on and carrying current.
- c3: Under voltage detect ( $UV_{BSD}$ ).
- c4: IGBT turn off in spite of control input condition, but there is no fault signal output.
- c5: Under voltage reset ( $UV_{BSR}$ ).
- c6: Normal operation: IGBT turn on and carrying current.

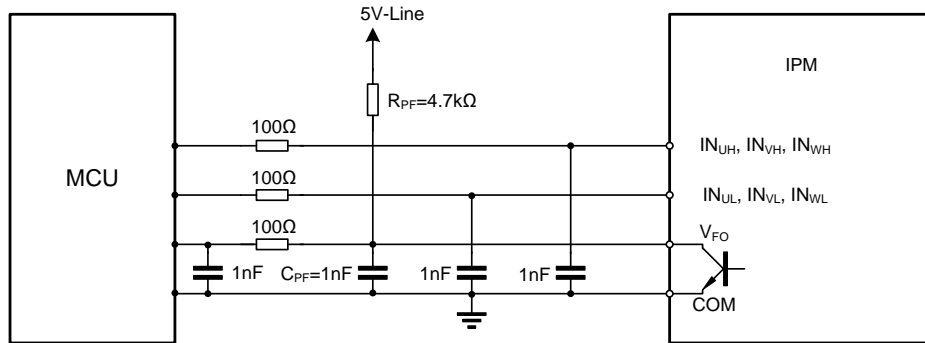


Fig.6 MCU input/output connection circuit recommended

**Note:**

The RC coupling of each input should change following the PWM control solution and the PCB connection impedance. There is a 5K pull-down resistor connected to IPM input, and attention should be paid to the voltage drop at the input when the external filter resistor is used.

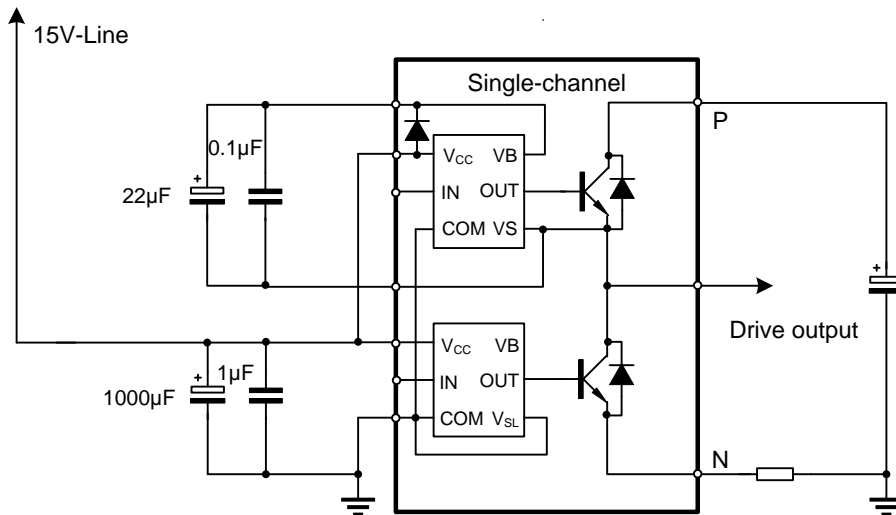
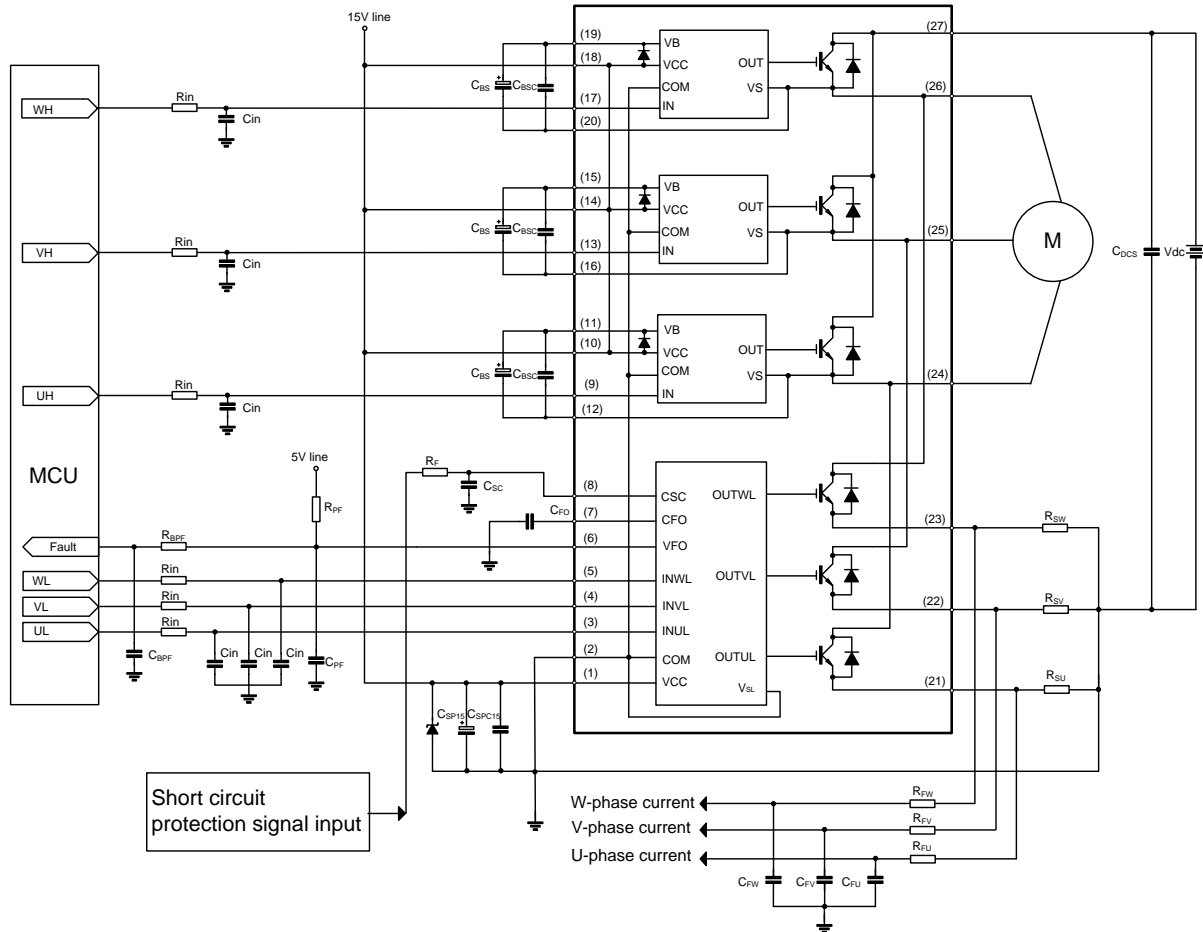


Fig.7 Bootstrap circuit and parameter setting recommended

**Note:**

1. The bootstrap capacitance should change following the PWM control solution;
2. Ceramic capacitor between  $V_{CC}$  and COM must be more than  $1\mu F$  and should be close to the pin of the power module as near as possible.

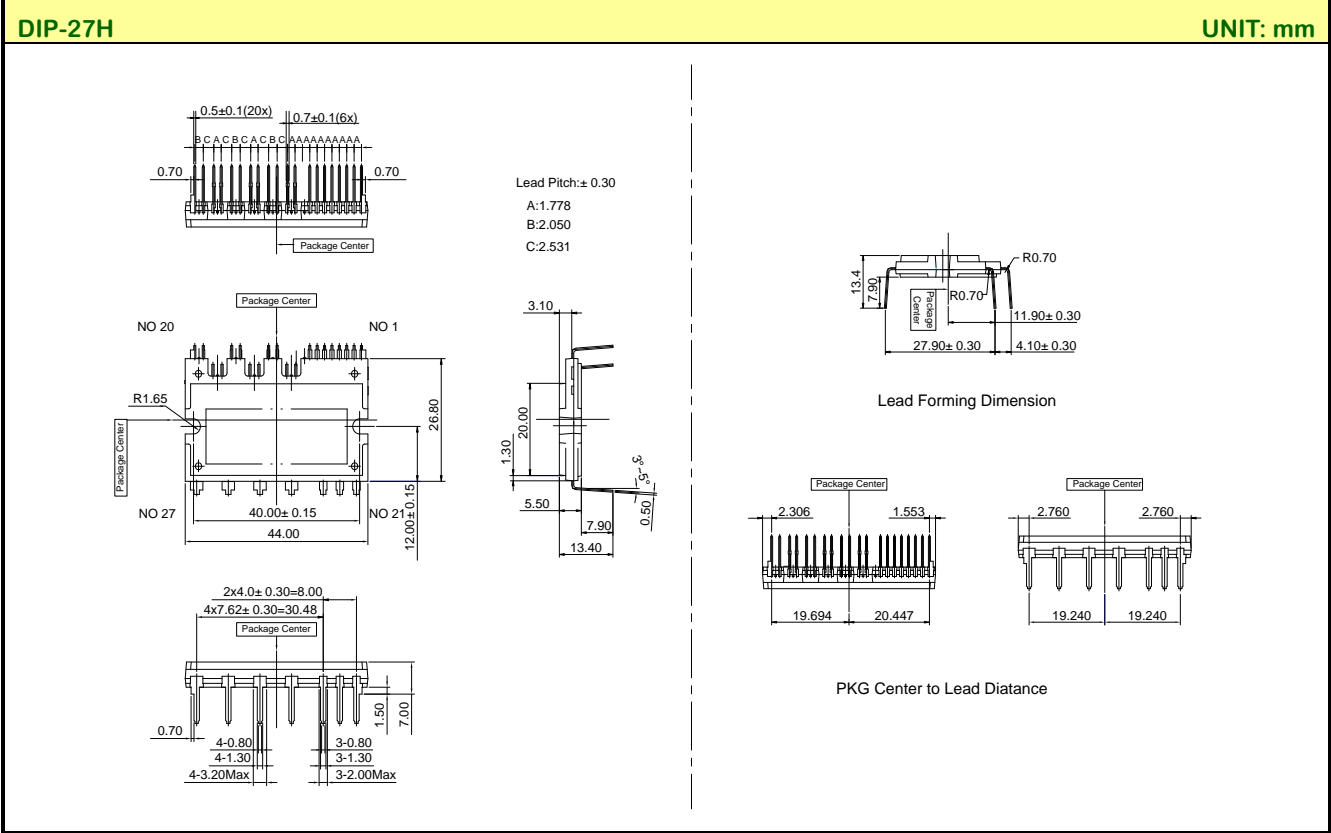
**TYPICAL APPLICATION CIRCUIT**



**Note:**

- (1) The routing of each input pin should be as short as possible to avoid the possible error action;
- (2) Input signal is high active and there is a 5K $\Omega$  pull-down resistor connected to the ground at input of each channel in the HVIC; In addition, RC filter circuit can be added to the input, which will prevent the surge noise caused by the incorrect input. The time constant of Rin Cin is selected between 50 and 150nS with Cin not less than 1nF( $R_{in}=100\Omega$  ,  $C_{in}=1nF$  are recommended) ;
- (3) To avoid the surge damage, a flat high-frequency non-inductive capacitor between 0.1 $\mu F$  and 0.22 $\mu F$  should be connected between PN and the routing must be as short as possible;
- (4) The routing between current detect resistor and IPM should be as short as possible to avoid the damage caused by the big surge voltage bringing from the connection inductance.
- (5) A filter capacitor at least 7 times by bootstrap capacitor CBS is better to be added at the 15V power supply input;
- (6) Each external capacitor must be connected to the pins of IPM as near as possible;
- (7)  $V_{FO}$  output is open and an external 4.7k $\Omega$  resistor pulled up to 5V is needed;
- (8)  $V_{FO}$  fault output pulse width  $t_{FO}$  is decided by  $C_{FO}$ ,  $C_{FO}=18.3 \times 10^{-6} \times t_{FO}[F]$ , if  $C_{FO}=33nF$ , then  $t_{FO}=1.8ms$  (typ);
- (9) In short circuit protection circuit, please select the time constant of RF and CSC between 1.5~2  $\mu s$ , at the same time, the routing around the RF and CSC should be as short as possible.

**PACKAGE OUTLINE**



**Important notice :**

1. The instructions are subject to change without notice !
2. Customers should obtain the latest relevant information before placing orders and should verify that such information is complete and current. Please read the instructions carefully before using our products, including the circuit operation precautions.
3. Our products are consumer electronic products or the other civil electronic products.
4. When using our products, please do not exceed the maximum rating of the products, otherwise the reliability of the whole machine will be affected. There is a certain possibility of failure or malfunction of any semiconductor product under specific conditions. The buyer is responsible for complying with safety standards and taking safety measures when using our products for system design, sample and whole machine manufacturing, so as to avoid potential failure risk that may cause personal injury or property loss.
5. It is strongly recommended to identify the trademark when buying our products. Please contact us if there is any question.
6. Product promotion is endless, our company will wholeheartedly provide customers with better products!
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Rev: 1.2

Revision History:

1. Update package outline diagram and important notice
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Rev: 1.1

Revision History:

1. Modify Characteristic
- 

Rev: 1.0

Revision History:

1. First release
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